

BAS28

High-speed double diode Rev. 3 — 22 July 2010

Product data sheet

Product profile

1.1 General description

Two high-speed switching diodes fabricated in planar technology, and encapsulated in a small SOT143B Surface-Mounted Device (SMD) plastic package. The diodes are not connected.

1.2 Features and benefits

■ High switching speed: $t_{rr} \le 4$ ns

Reverse voltage: V_R ≤ 75 V

Repetitive peak reverse voltage: V_{RRM} ≤ 85 V Repetitive peak forward current: I_{FRM} ≤ 500 mA

AEC-Q101 qualified

Small SMD package

1.3 Applications

High-speed switching in e.g. surface-mounted circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
l _F	forward current		<u>[1]</u> _	-	215	mA
I _R	reverse current	V _R = 75 V	-	-	1	μΑ
V_R	reverse voltage		-	-	75	V
t _{rr}	reverse recovery time		[2] _	-	4	ns

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.



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2. Pinning information

Table 2. Pinning

Table 2.	i iiiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	cathode (diode 1)		
2	cathode (diode 2)	4 3	4 3
3	anode (diode 2)		
4	anode (diode 1)	1 2	$egin{bmatrix} abla & abla \\ $
			1 2
			006aab100

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BAS28	-	plastic surface-mounted package; 4 leads	SOT143B	

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BAS28	JT*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V _{RRM}	repetitive peak reverse voltage		-	85	V
V_R	reverse voltage		-	75	V
I _F	forward current		<u>[1]</u> _	215	mA
I _{FRM}	repetitive peak forward current		-	500	mA
I _{FSM}	non-repetitive peak forward current	square wave	[3]		
		t _p = 1 μs	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		t _p = 1 s	-	0.5	Α
Per device					
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1][2]	250	mW
Tj	junction temperature		-	150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 PCB.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device;	one diode loaded					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	360	K/W

^[1] Device mounted on an FR4 PCB.

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^[2] One diode loaded.

^[3] $T_j = 25$ °C prior to surge.

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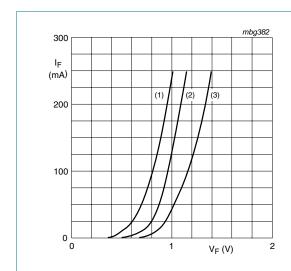
7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

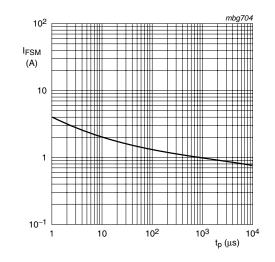
· amb = 0	C direction and opposition.					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode)					
V _F	forward voltage	$I_F = 1 \text{ mA}$	-	-	715	mV
		I _F = 10 mA	-	-	855	mV
		$I_F = 50 \text{ mA}$	-	-	1	V
		I _F = 150 mA	-	-	1.25	V
I _R	reverse current	V _R = 25 V	-	-	30	nA
		V _R = 75 V	-	-	1	μΑ
		V _R = 25 V; T _j = 150 °C	-	-	30	μΑ
		V _R = 75 V; T _j = 150 °C	-	-	50	μΑ
C _d	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
t _{rr}	reverse recovery time		[1] _	-	4	ns
V_{FR}	forward recovery voltage		[2] _	-	1.75	V

- [1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.
- [2] When switched from $I_F = 10$ mA; $t_r = 20$ ns.



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 25 \,^{\circ}C$; typical values
- (3) $T_j = 25$ °C; maximum values

Fig 1. Forward current as a function of forward voltage



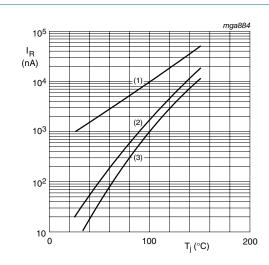
Based on square wave currents.

T_j = 25 °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values

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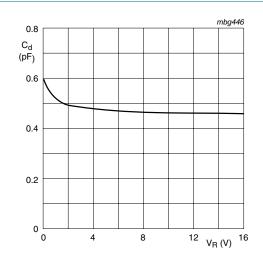
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 $V_R = V_{Rmax}$

- (1) $V_R = 75 \text{ V}$; maximum values
- (2) V_R = 75 V; typical values
- (3) $V_R = 25 V$; typical values

Fig 3. Reverse current as a function of junction temperature



f = 1 MHz; T_j = 25 °C

Fig 4. Diode capacitance as a function of reverse voltage; typical values

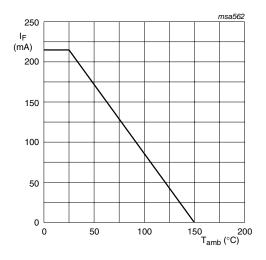
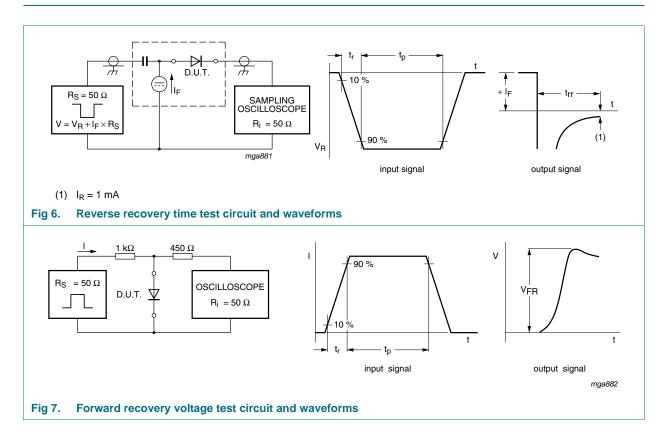


Fig 5. Forward current as a function of ambient temperature; derating curve

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8. Test information

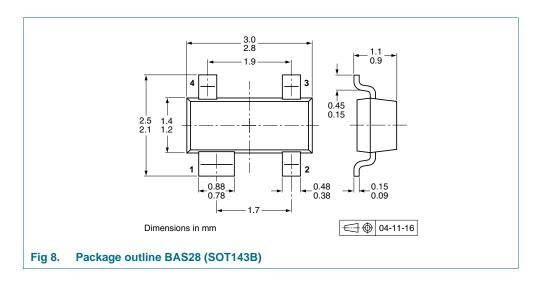


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Packing information

Table 8. Packing methods

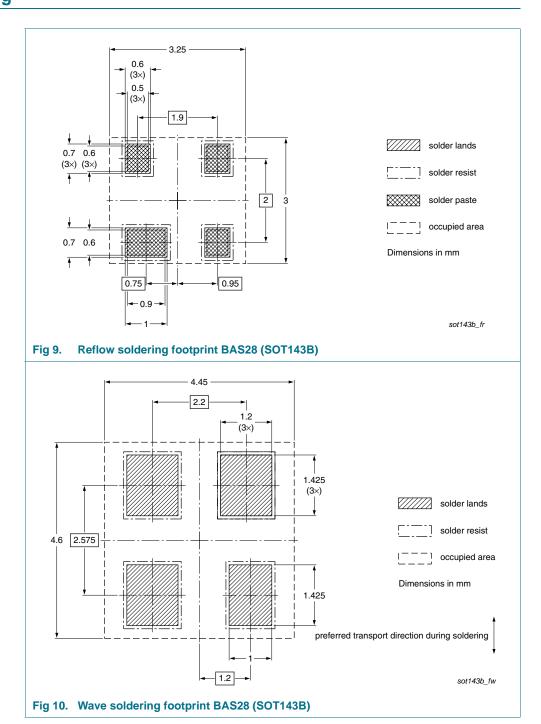
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BAS28	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BAS28 v.3	20100722	Product data sheet	-	BAS28_2	
Modifications:		f this data sheet has been re NXP Semiconductors.	designed to comply w	ith the new identity	
	 Legal texts h 	ave been adapted to the new	company name whe	re appropriate.	
	 Section 1.1 " 	General description": amende	ed		
	 Section 4 "M 	arking": updated			
	 Table 1 "Quick reference data": added Section 8 "Test information": added 				
• Figure 8: superseded by minimized package outline drawing					
	 Section 10 "F 	Packing information": added			
	 Section 11 "S 	Soldering": added			
	 Section 13 "L 	<u>egal information"</u> : updated			
BAS28_2	19960910	Product specification	-	BAS28_1	
BAS28_1	19960403	Product specification	-	-	

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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